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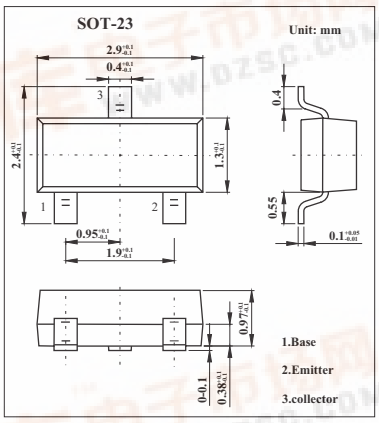
# Silicon NPN Epitaxial

# 2SC2776




## ■ Features

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## ■ Absolute Maximum Ratings Ta = 25℃

| Parameter | Symbol | Rating | Unit |
|---|---|---|---|
| Collector-base voltage | $V_{CBO}$ | 30 | V |
| Collector-emitter voltage | $V_{CEO}$ | 20 | V |
| Emitter-base voltage | $V_{EBO}$ | 4 | V |
| Collector current | $I_C$ | 30 | mA |
| Collector power dissipation | $P_C$ | 100 | mW |
| Junction temperature | $T_j$ | 150 | ℃ |
| Storage temperature | $T_{stg}$ | -55 to +150 | ℃ |

## ■ Electrical Characteristics Ta = 25℃

| Parameter | Symbol | Testconditons | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C$ = 10μA , $I_E$ = 0 | 30 | | | V |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C$ = 1mA , $R_{BE}$ = ∞ | 20 | | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E$ = 10μA , $I_C$ = 0 | 4 | | | V |
| Collector cutoff current | $I_{CBO}$ | $V_{CB}$ = 10V, $I_C$ = 0 | | | 0.5 | μA |
| DC current transfer ratio | $h_{FE}$ | $V_{CE}$ = 6 V, $I_C$ = 1 mA | 35 | | 200 | |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | $I_C$ = 10 mA, $I_B$ = 1 mA | | 0.8 | 1.2 | V |
| Collector output capacitance | $C_{ob}$ | $V_{CB}$ = 10 V, $I_E$ = 0, f = 1 MHz | | 1.1 | | pF |
| Gain bandwidth product | $f_T$ | $V_{CE}$ = 6 V, $I_C$ = 1 MA | | 320 | | MHz |
| Noise figure | NF | $V_{CE}$ = 6 V, $I_C$ = 1 mA, f = 100 MHz, Rg = 50 Ω | | 5.5 | | dB |
| Power gain | PG | $V_{CE}$ = 6 V, $I_C$ = 1 mA, f = 100 MHz, $R_g$ = 100Ω, $R_L$ = 550Ω | | 17 | | dB |

## ■ $h_{FE}$ Classification

| Marking | VA | VB | VC |
|---|---|---|---|
| Rank | A | B | C |
| hFE | 35～70 | 60～120 | 100～200 |

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